

SRNT <=

TC 3700 Inventor Search Program

See attached inventor searches for applications and /or patents to help resolve questions of overlapping subject mater. These searches are provided an an initial examination aid: examiners should perform updated or expanded PALM or EAST inventors searches as appropriate.

Serial Number: 11/019,287

- 1) See attached printout of inventors listed in PALM**
- 2) See attached EAST Inventor Search Printout shows Inventor search terms**

Day : Tuesday
Date: 4/10/2007

Time: 10:11:29

 PALM INTRANET

Inventor Information for 11/019287

Inventor Name	City	State/Country
YOO, JAE-YOO	GWANGMYEONG	KOREA, REPUBLIC OF
LEE, CHEL-WOONG	SEOUL	KOREA, REPUBLIC OF
SUNG, JI-WON	SEOUL	KOREA, REPUBLIC OF
KIM, HYUNG-JIN	SEOUL	KOREA, REPUBLIC OF

[Appln Info](#)[Contents](#)[Petition Info](#)[Atty/Agent Info](#)[Continuity/Reexam](#)[Foreign I](#)Search Another: Application# or Patent# PCT / / or PG PUBS # Attorney Docket # Bar Code #

To go back use Back button on your browser toolbar.

Back to [PALM](#) | [ASSIGNMENT](#) | [OASIS](#) | [Home page](#)

1	US 7101776 B2	20060905	Method of fabricating MOS transistor using total gate silicidation process	438/592	257/E21.203; 257/E21.438; 257/E21.444; 257/E21.634; 257/E21.636; 257/E29.161; 438/595; 438/655	Yoo; Jae-Yoon et al.
1	US 7084041 B2	20060801	Bipolar device and method of manufacturing the same including pre-treatment using germane gas	438/343	257/E21.379; 257/E29.03; 257/E29.191; 257/E29.193; 438/488; 438/494	Rhee; Hwa-sung et al.
1	US 7033895 B2	20060425	Method of fabricating a MOS transistor with elevated source/drain structure using a selective epitaxial growth process	438/300	257/E21.409; 257/E21.43; 257/E29.267; 438/184; 438/230; 438/301; 438/305; 438/306; 438/363	Lee; Seung-hwan et al.
1	US 6987310 B2	20060117	Multi-layered structure including an epitaxial layer having a low dislocation defect density, semiconductor device comprising the same, and method of fabricating the semiconductor device	257/616	257/190; 257/191; 257/192; 257/E21.125; 257/E21.129	Lee; Ho et al.
1	US 6930462 B2	20050816	Apparatus and method for controlling	318/632	318/556; 417/44.1; 417/44.11;	Yoo; Jae Yoo et al.

			operation of compressor		417/45; 417/53; 62/156; 62/228.1; 62/6	
1	US 6878575 B2	20050412	Method of forming gate oxide layer in semiconductor devices	438/142	134/2; 134/3; 257/E21.193; 257/E21.268	Yoo; Jae-Yoon et al.
1	US 6851934 B2	20050208	Stroke control apparatus of reciprocating compressor and method thereof	417/44.11	417/44.1; 417/53	Yoo; Jae-Yoo et al.
1	US 6835621 B2	20041228	Method of fabricating non-volatile memory device having a structure of silicon-oxide-nitride-oxide-silicon	438/261	257/E21.21; 257/E21.268; 257/E21.279; 257/E21.301; 257/E21.423; 257/E21.679; 257/E27.103; 438/287	Yoo; Jae-yoon et al.
1	US 6815922 B2	20041109	Apparatus and method for controlling operation of compressor	318/632	318/556; 417/44.1; 417/44.11; 417/45; 417/53; 62/156; 62/228.1; 62/6	Yoo; Jae Yoo et al.
1	US 6685438 B2	20040203	Apparatus and method for controlling operation of reciprocating compressor	417/44.11	417/22; 417/415; 417/44.1; 417/44.8; 417/45; 417/53	Yoo; Jae Yoo et al.
1	US 6682310 B2	20040127	Apparatus and method for controlling operation of reciprocating motor compressor	417/42	318/687; 417/212; 417/44.1; 417/44.11; 417/45	Yoo; Jae-Yoo et al.

1	US 6624496 B2	20030923	Method of forming T-shaped isolation layer, method of forming elevated salicide source/drain region using the same, and semiconductor device having T-shaped isolation layer	257/510	257/E21.549; 257/E21.628; 438/301; 438/427	Ku; Ja-Hum et al.
1	US 6616414 B2	20030909	Apparatus and method for controlling a compressor	417/44.1	62/160	Yoo; Jae Yoo et al.
1	US 6565327 B2	20030520	Circuit for driving linear compressor	417/44.1	417/417; 417/44.11	Yoo; Jae Yoo et al.
1	US 6541953 B2	20030401	Apparatus for detecting shaking of stroke of linear compressor and method therefor	324/76.52	417/44.11	Yoo; Yoo Jae et al.
1	US 6520746 B2	20030218	Apparatus and method for controlling operation of reciprocating compressor	417/44.11	417/18; 417/212; 417/417; 417/44.1; 417/45; 417/53	Yoo; Jae Yoo et al.
1	US 6486039 B2	20021126	Method of fabricating a trench isolation structure having sidewall oxide layers with different thicknesses	438/425	257/E21.548; 257/E21.551; 438/427; 438/433; 438/696; 438/704; 438/717; 438/719; 438/723; 438/724	Yoo; Jae-yoon et al.

1	US 6383877 B1	20020507	Method of forming T-shaped isolation layer, method of forming elevated salicide source/drain region using the same, and semiconductor device having T-shaped isolation layer	438/296	257/E21.165; 257/E21.431; 257/E21.438; 257/E21.549; 257/E21.628; 438/300; 438/301; 438/427; 438/682	Ahn; Dong-ho et al.
---	---------------------	----------	--	---------	---	---------------------------